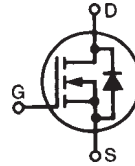


TrenchMV™ Power MOSFET

IXTH200N10T IXTQ200N10T

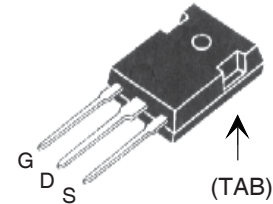
$V_{DSS} = 100V$
 $I_{D25} = 200A$
 $R_{DS(on)} \leq 5.5m\Omega$

N-Channel Enhancement Mode
 Avalanche Rated

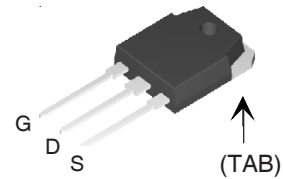


| Symbol | Test Conditions | Maximum Ratings | |
|------------|---|-----------------|--------------------------|
| V_{DSS} | $T_J = 25^\circ C$ to $175^\circ C$ | 100 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$ | 100 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ C$ | 200 | A |
| I_{LRMS} | Lead Current Limit, RMS | 75 | A |
| I_{DM} | $T_C = 25^\circ C$, pulse width limited by T_{JM} | 500 | A |
| I_A | $T_C = 25^\circ C$ | 40 | A |
| E_{AS} | $T_C = 25^\circ C$ | 1.5 | J |
| P_D | $T_C = 25^\circ C$ | 550 | W |
| T_J | | -55 ... +175 | $^\circ C$ |
| T_{JM} | | 175 | $^\circ C$ |
| T_{stg} | | -55 ... +175 | $^\circ C$ |
| T_L | 1.6mm (0.062in.) from case for 10s Plastic body for 10 seconds | 300 260 | $^\circ C$ $^\circ C$ |
| M_d | Mounting torque | 1.13 / 10 | Nm/lb.in. |
| Weight | TO-247 | 6.0 | g |
| | TO-3P | 5.5 | g |

TO-247 (IXTH)



TO-3P (IXTQ)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- International standard packages
- 175°C Operating Temperature
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - High Side Switch
 - 12V Battery
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary - Side Switch
- High Current Switching Applications

| Symbol | Test Conditions | Characteristic Values | | |
|--------------|---|-----------------------|------|----------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 100 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 2.5 | | 4.5 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$ | | | 5 μA |
| | $V_{GS} = 0V$ $T_J = 150^\circ C$ | | | 250 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 50A$, Notes 1, 2 | 4.5 | | 5.5 m Ω |

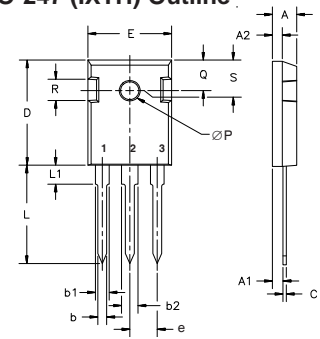
| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1 | 60 | 96 | S |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 9400 | pF |
| C_{oss} | | | 1087 | pF |
| C_{rss} | | | 140 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 50\text{A}$ $R_G = 3.3\Omega$ (External) | | 35 | ns |
| t_r | | | 31 | ns |
| $t_{d(off)}$ | | | 45 | ns |
| t_f | | | 34 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 50\text{A}$ | | 152 | nC |
| Q_{gs} | | | 47 | nC |
| Q_{gd} | | | 47 | nC |
| R_{thJC} | | | 0.27 | $^\circ\text{C/W}$ |
| R_{thCH} | | 0.25 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|----------|---|-----------------------|------|-------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 200 A |
| I_{SM} | Repetitive, Pulse width limited by T_{JM} | | | 500 A |
| V_{SD} | $I_F = 50\text{A}$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.0 V |
| t_{rr} | $I_F = 100\text{A}$, $V_{GS} = 0\text{V}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 50\text{V}$ | | 76 | ns |
| Q_{RM} | | | 205 | nC |
| I_{RM} | | | 5.4 | A |

- Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

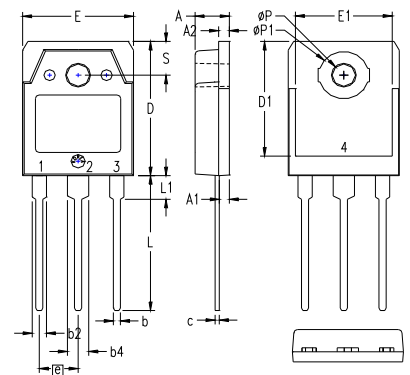
TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ØP | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |

TO-3P (IXTQ) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4, TAB - Drain

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .185 | .193 | 4.70 | 4.90 |
| A1 | .051 | .059 | 1.30 | 1.50 |
| A2 | .057 | .065 | 1.45 | 1.65 |
| b | .035 | .045 | 0.90 | 1.15 |
| b2 | .075 | .087 | 1.90 | 2.20 |
| b4 | .114 | .126 | 2.90 | 3.20 |
| c | .022 | .031 | 0.55 | 0.80 |
| D | .780 | .791 | 19.80 | 20.10 |
| D1 | .665 | .677 | 16.90 | 17.20 |
| E | .610 | .622 | 15.50 | 15.80 |
| E1 | .531 | .539 | 13.50 | 13.70 |
| e | .215 BSC | | 5.45 BSC | |
| L | .779 | .795 | 19.80 | 20.20 |
| L1 | .134 | .142 | 3.40 | 3.60 |
| ØP | .126 | .134 | 3.20 | 3.40 |
| ØP1 | .272 | .280 | 6.90 | 7.10 |
| S | .193 | .201 | 4.90 | 5.10 |

All metal area are tin plated.

IXYS reserves the right to change limits, test conditions, and dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ 25°C

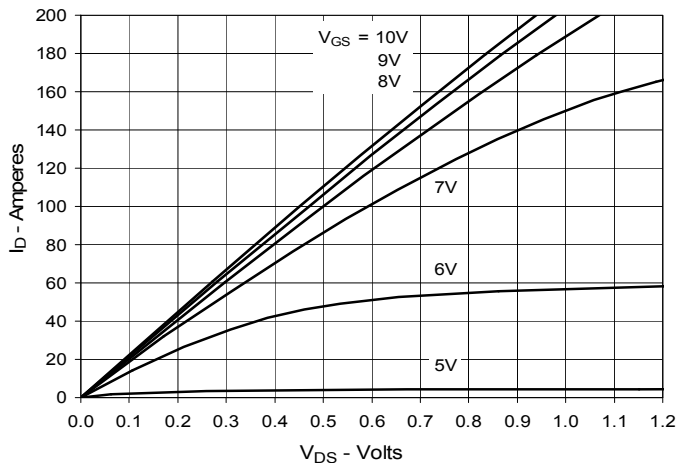


Fig. 2. Extended Output Characteristics @ 25°C

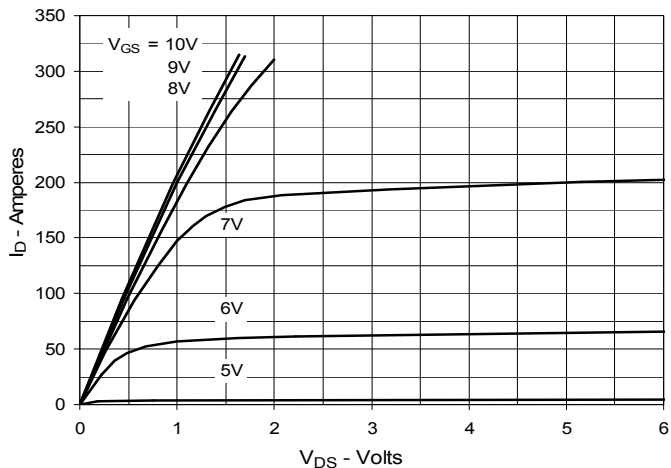


Fig. 3. Output Characteristics @ 150°C

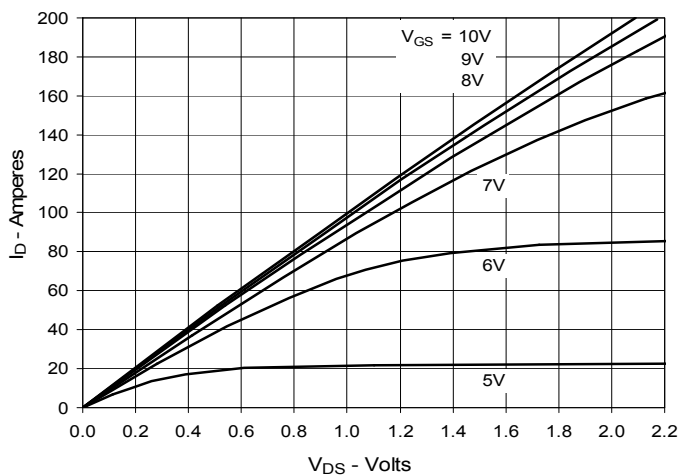


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 100A$ Value vs. Junction Temperature

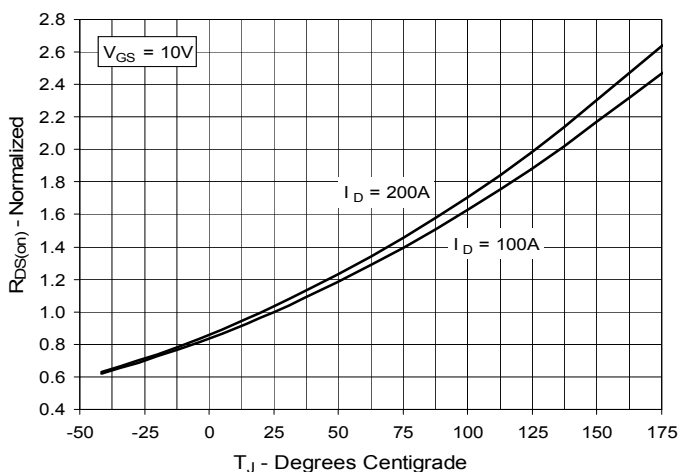


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 100A$ Value vs. Drain Current

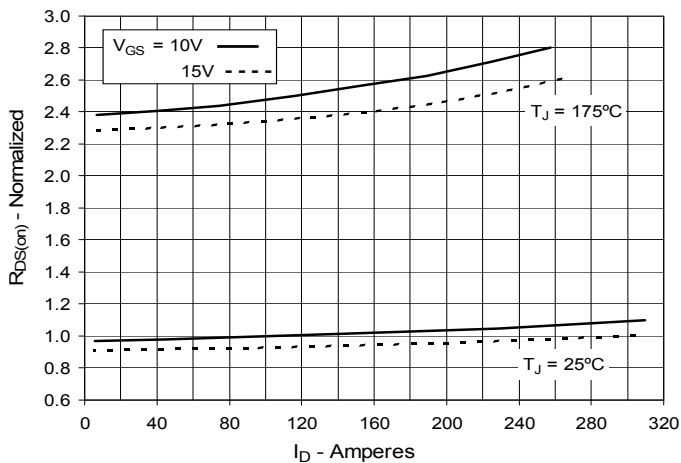


Fig. 6. Drain Current vs. Case Temperature

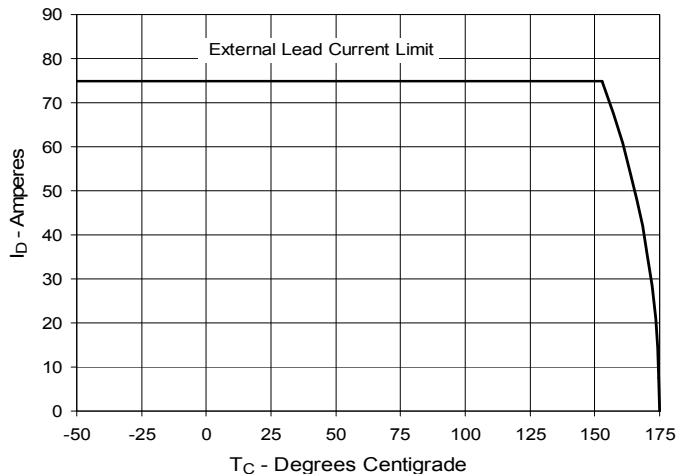


Fig. 7. Input Admittance

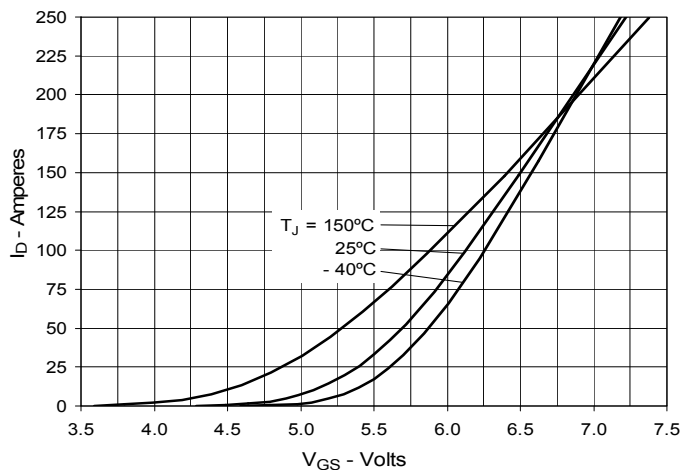


Fig. 8. Transconductance

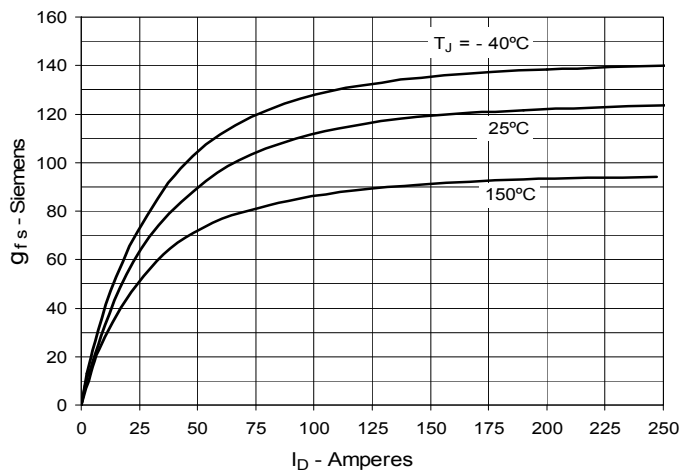


Fig. 9. Forward Voltage Drop of Intrinsic Diode

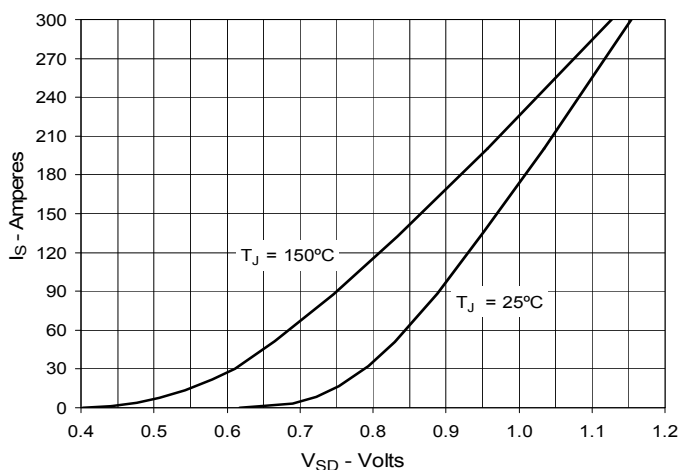


Fig. 10. Gate Charge

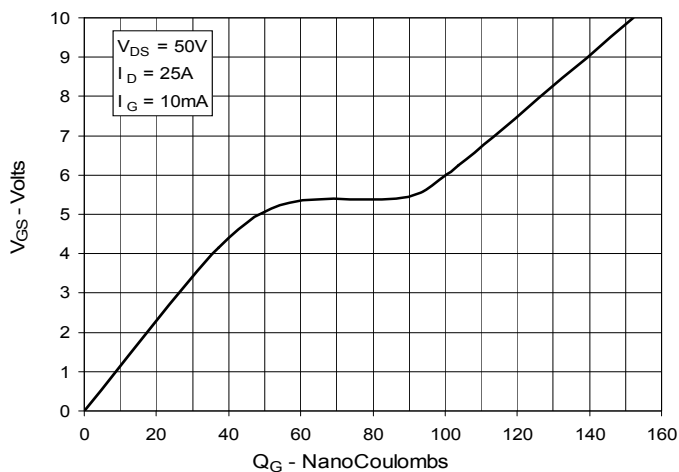


Fig. 11. Capacitance

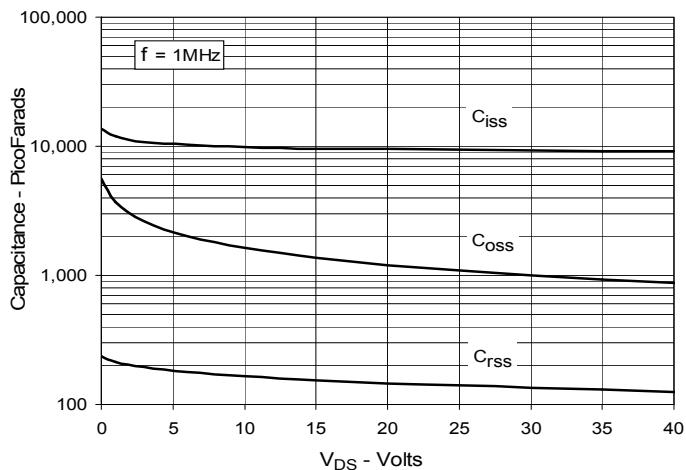


Fig. 12. Maximum Transient Thermal Impedance

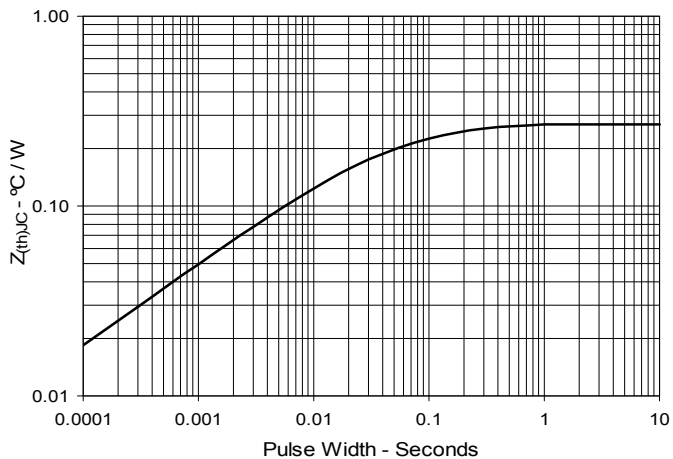


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

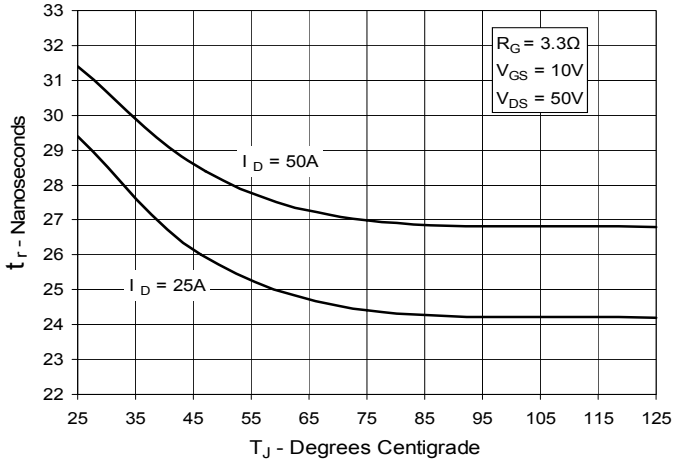


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

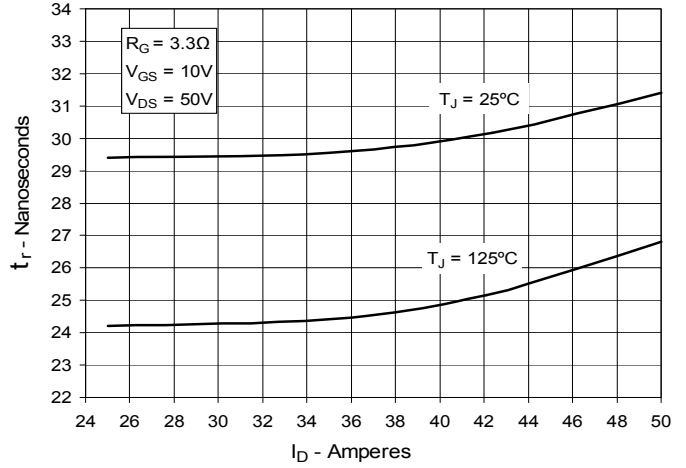


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

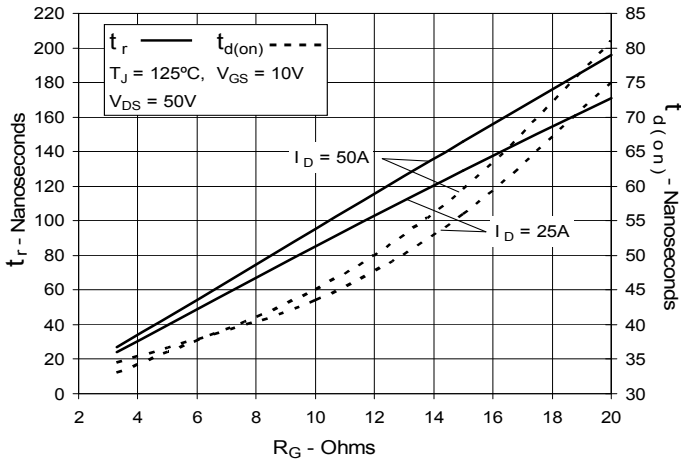


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

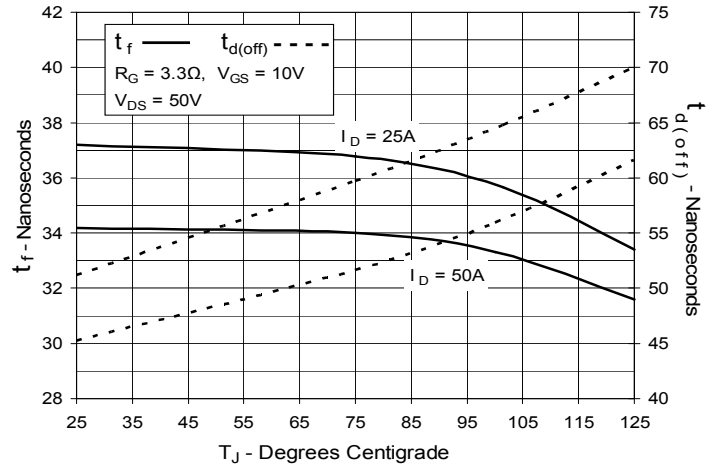


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

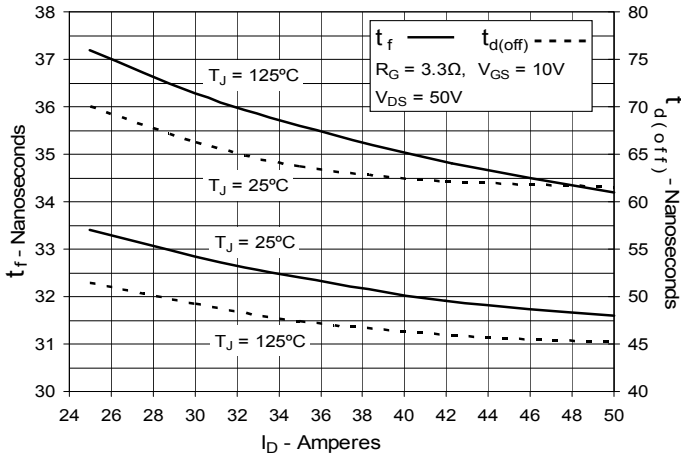


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

